IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

2. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film, and

wherein the thickness of the first leveling film is 0.1 μm or more and less than 1.5 μm.

3. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film, and

wherein the thickness of the second leveling film is from 0.1 μm to 2.9 μm inclusive.

4. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film, and

wherein the total thickness of the first leveling film and the second leveling film is from 0.2 μm to 3.0 μm.

5. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film, and

wherein the first leveling film and the second leveling film are insulating films formed by spin coating.

6. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a wiring over the gate wiring;

forming a first leveling film containing a siloxane structure over the wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

7. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure over the gate wiring;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film, and

wherein the first leveling film and the second leveling film comprise the same material.

8. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film of a resin containing a siloxane structure over the gate wiring;

forming a second leveling film of a resin containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

9. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a insulating film comprising an inorganic material over the gate insulating film;

forming a first leveling film containing a siloxane structure over the insulating film;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

10. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

applying a first layer containing a siloxane structure by spin coating;

baking the first layer to form a first leveling film;

applying a second layer containing a siloxane structure by spin coating;

baking the second layer to form a second leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

11. (canceled)

12. (previously presented) The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

13. (canceled)

14. (previously presented) The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. (canceled)

16. (previously presented) The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. (canceled)

18. (previously presented) The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (canceled)

20. (previously presented) The method according to claim 5, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (canceled)

22. (previously presented) The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (canceled)

24. (previously presented) The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (canceled)

26. (previously presented) The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (canceled)

28. (previously presented) The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29. (canceled)

30. (previously presented) The method according to claim 10, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

31. (previously presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first inorganic film on the gate wiring;

forming a wiring on the first inorganic film;

forming a second inorganic film on the wiring;

forming a first leveling film containing a siloxane structure on the second inorganic film;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film; and

forming an EL layer over the pixel electrode,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

32. (previously presented) The method according to claim 31, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

33. (new) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming a gate insulating film on the semiconductor film;

forming a gate wiring on the gate insulating film;

forming a first leveling film containing a siloxane structure on the second inorganic film;

forming a second leveling film containing a siloxane structure on the first leveling film;

forming a pixel electrode on the second leveling film;

forming an EL layer over the pixel electrode; and

enclosing the EL layer by sealing materials with a space between the EL layer and the sealing materials filled by a filler,

wherein the thickness of the first leveling film is thinner than that of the second leveling film.

34. (new) The method according to claim 33, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.